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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										外形	備考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αb} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
- 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)										外 形	備 考		
				V _{CB0} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値 (μA)	V _{CE} (V)	直流又はハルス h _{FE} V _{CE} (V)	I _C (mA)	バイアス V _{CB} (V)	I _E (mA)	h _{fe} h _{fe} *	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μU)			f _{βT} f _{βT} * (Mc)	C _{ob} (pF)
★ 2SD266	オリジソ	PA. SW	Si. T	800	10	6 A	100W (T _c =25°C)	150	2mA	800	40	5	3 A								102	
" 267	"	"	"																			
" 268	"	"	"																			
" 269	"	"	"																			
" 270	"	"	"																			
★ " 271	オリジソ	PA	Si. T	800	10	2 A	30W (T _c =25°C)	150	2mA	800	20	5	1 A	12	-500				f _β 150kHz			100
★ " 272	"	"	"	800	10	2 A	30W (T _c =25°C)	150	2mA	800	40	5	1 A	12	-500				f _β 150kHz			100
★ " 273	"	PA. SW	"	800	10	5 A	80W (T _c =25°C)	150	2mA	800	20	5	2 A	12	-1 A				f _β 150kHz			102
★ " 274	"	"	"	800	10	5 A	80W (T _c =25°C)	150	2mA	800	40	5	2 A	12	-1 A				f _β 150kHz			102
" 275	"	"	"																			
" 276	"	"	"																			
" 277	"	"	"																			
" 278	"	"	"																			
" 279	"	"	"																			
" 280	"	"	"																			
" 281	"	"	"																			
" 282	"	"	"																			
★ " 283	日 電	PA. SW	Si. E	120	5	5 A	25 W (T _c =25°C)	150	200	40	55	1	5 A									134
" 284	"	"	"	120	5	5 A	25 W (T _c =25°C)	150	200	40	80	5	1 A	10	-100				20 *			134 2SB550 シリコン
★ " 285	"	"	"	100	5	5 A	25 W (T _c =25°C)	150	200	40	40	1	5 A									134
★ " 286	"	PA	Si. TMe	180	7	10 A	100W (T _c =25°C)	150	300	100	75	5	2 A									102
★ " 287	"	"	"	200	7	10 A	100W (T _c =25°C)	150	300	100	75	5	2 A									102
" 288	日 電	"	Si. T	80	5	3 A	20W (T _c =25°C)	150	10	60	100	5	500	5	-100				35 *	55		268
" 289	"	"	"	80	5	3 A	20W (T _c =25°C)	150	10	60	100	5	500	5	-100				35 *	55		267
★ " 290	ソニー	PA. SW	Si. TMe	80		5 A	10 W (T _c =25°C)	120	100	150	100	3	2 A									153
★ " 291	"	RF. PA	Si. DJ	70	10	3 A	18W (T _c =25°C)	150	20	30	100	1	100	10	-500				4 *	250		153
★ " 292	"	PA	"	70	10	3 A	18W (T _c =25°C)	150	20	30	100	1	100	10	-500				4 *	250		153
" 293	オリジソ	"	Si. T	800	10	10 A	125W (T _c =25°C)	150	3mA	800	20	5	5 A									102
" 294	"	"	"	800	10	10 A	125W (T _c =25°C)	150	3mA	800	40	5	5 A									102
" 295	オリジソ	PA. SW	Si. T	800	10	30 A	200W (T _c =25°C)	150	5mA	800	20	5	10 A	12	-2.5A				f _β 150kHz			154